



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23-3L Plastic-Encapsulate Transistors

2SB1198K TRANSISTOR (PNP)

FEATURES

- Low $V_{CE(sat)}$: $V_{CE(sat)} = -0.2V(Typ.) (I_C = -0.5A, I_B = -50mA)$
- High breakdown voltage $BV_{CEO} = -80V$
- Complements the 2SD1782K

SOT-23-3L



1. BASE
2. EMITTER
3. COLLECTOR

MAXIMUM RATINGS ($T_A = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-500	mA
P_C	Collector Power Dissipation	200	mW
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55-150	$^\circ C$

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50\mu A, I_E = 0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -2mA, I_B = 0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -50V, I_E = 0$			-0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-0.5	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -3V, I_C = -100mA$	120		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$			-0.5	V
Transition frequency	f_T	$V_{CE} = -10V, I_C = -50mA, f = 100MHz$		180		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		11		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	Q	R
Range	120-270	180-390
MARKING	AKQ	AKR

Typical Characteristics

2SB1198K

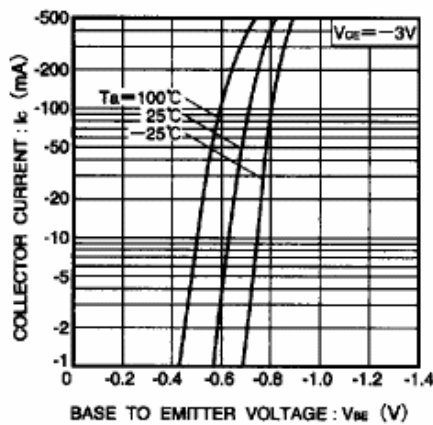


Fig.1 Grounded emitter propagation characteristics

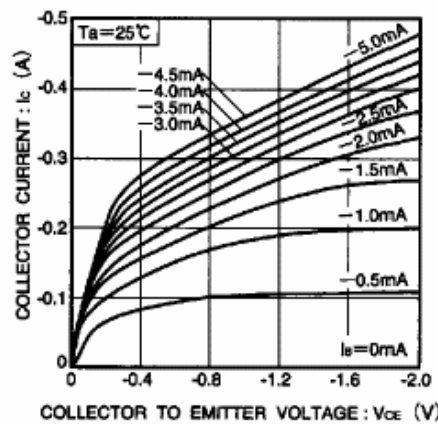


Fig.2 Grounded emitter output characteristics

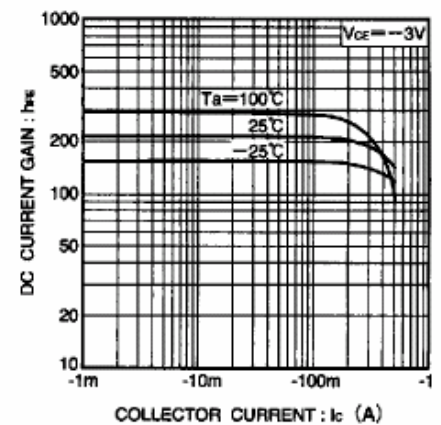


Fig.3 DC current gain vs. collector current

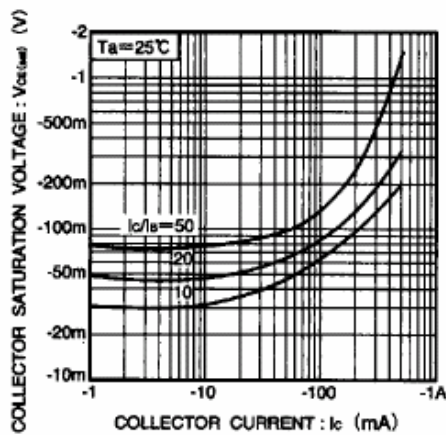


Fig.4 Collector-emitter saturation voltage vs. collector current (I)

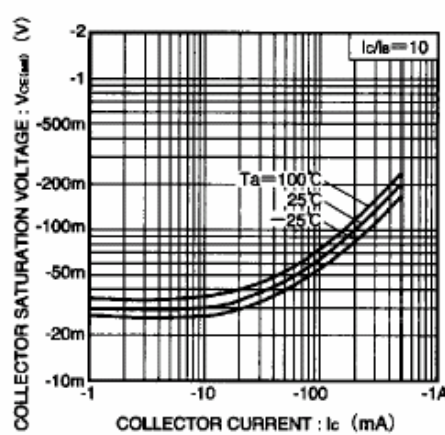


Fig.5 Collector-emitter saturation voltage vs. collector current (II)

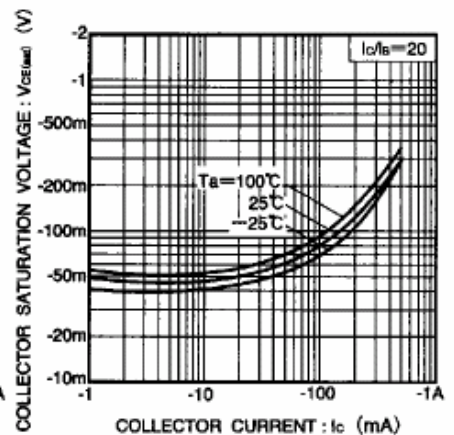


Fig.6 Collector-emitter saturation voltage vs. collector current (III)

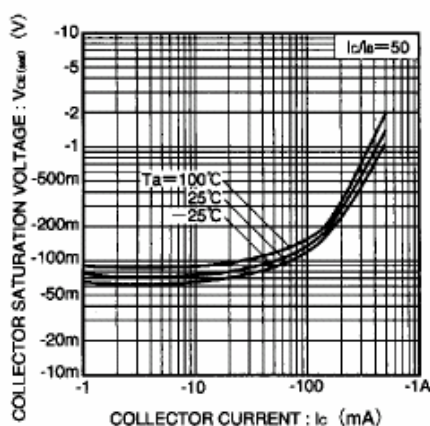


Fig.7 Collector-emitter saturation voltage vs. collector current (IV)

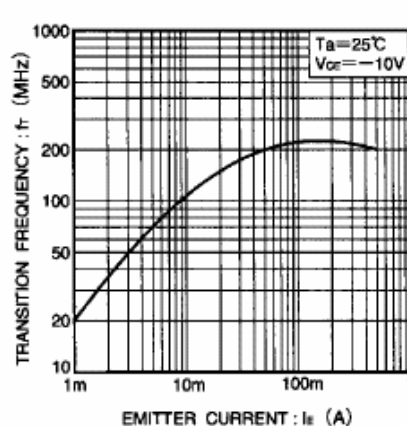


Fig.8 Gain bandwidth product vs. emitter current

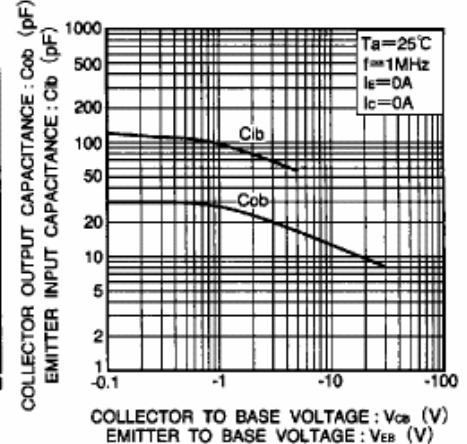


Fig.9 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage